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Electrochemically Tunable Mixed Valence Conduction in Ruthenium Hexacyanoruthenate

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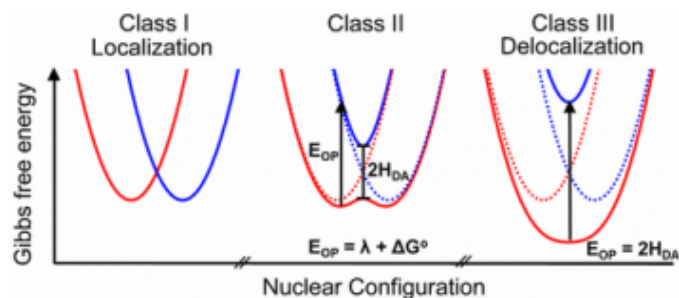
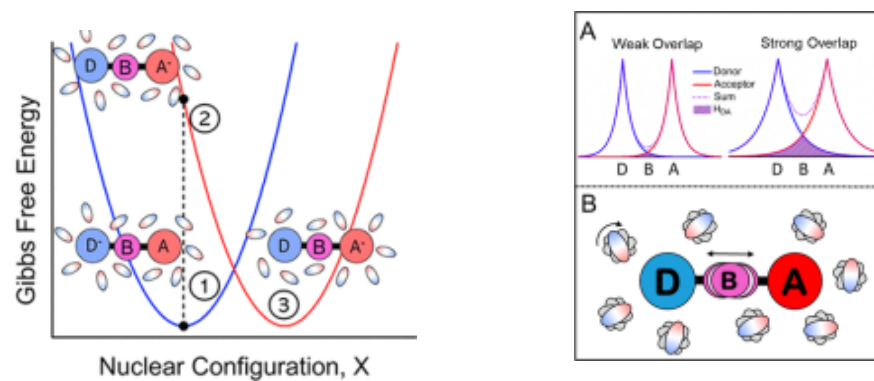
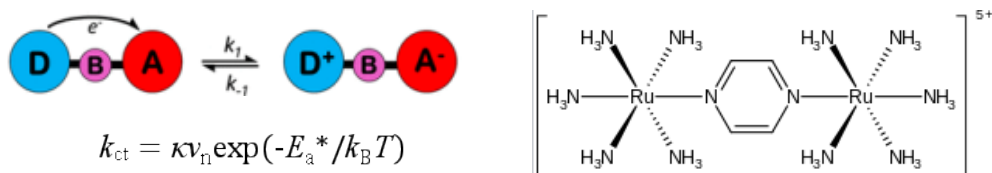
Intervalence Charge Transfer and Electronic Conduction



"We may consider mixed valence chemistry as the conceptual link between coordination chemistry and solid state physics." - Andreas Ludi

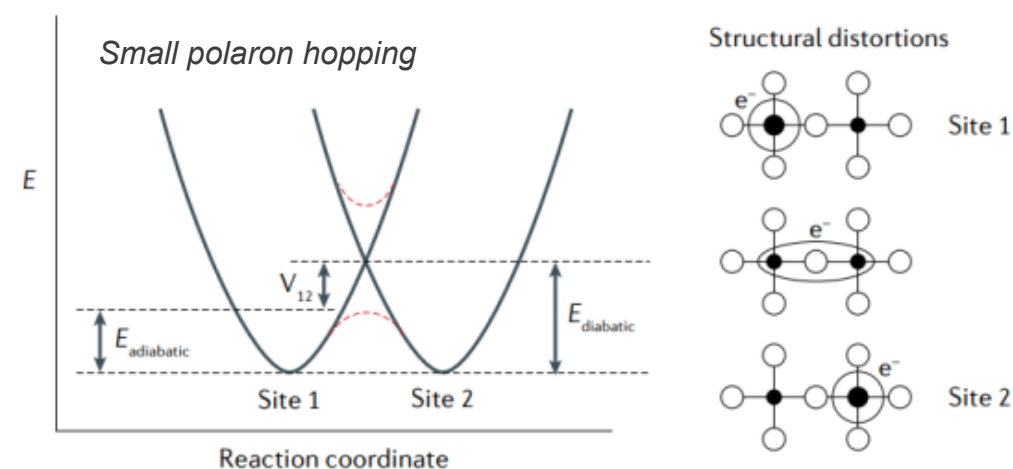
Ludi, A. Descriptive Chemistry of Mixed-Valence Compounds. In *Mixed-Valence Compounds: Theory and Applications in Chemistry, Physics, Geology, and Biology*, Brown, D. B. Ed.; Springer Netherlands, 1980; pp 25-47.

Coordination Chemistry (Electron Transfer Kinetics, Redox States, Donor-Bridge-Acceptor)

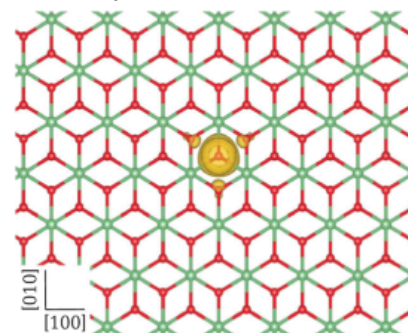


Piechota, E. J.; Meyer, G. J. *J. Chem. Educ.* **2019**, 96, 2450-2466.

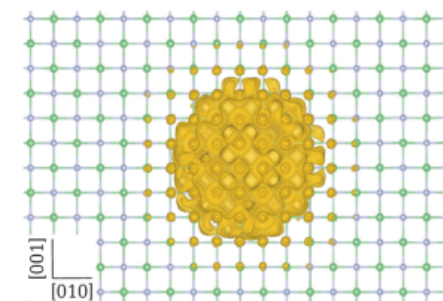
Solid State Physics (Electron Transport, Quasiparticles)



Small polaron



Large polaron



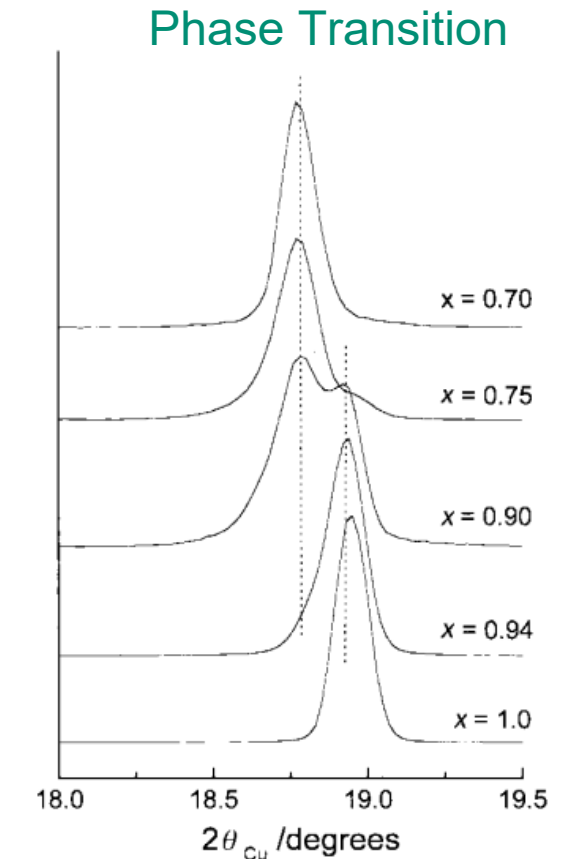
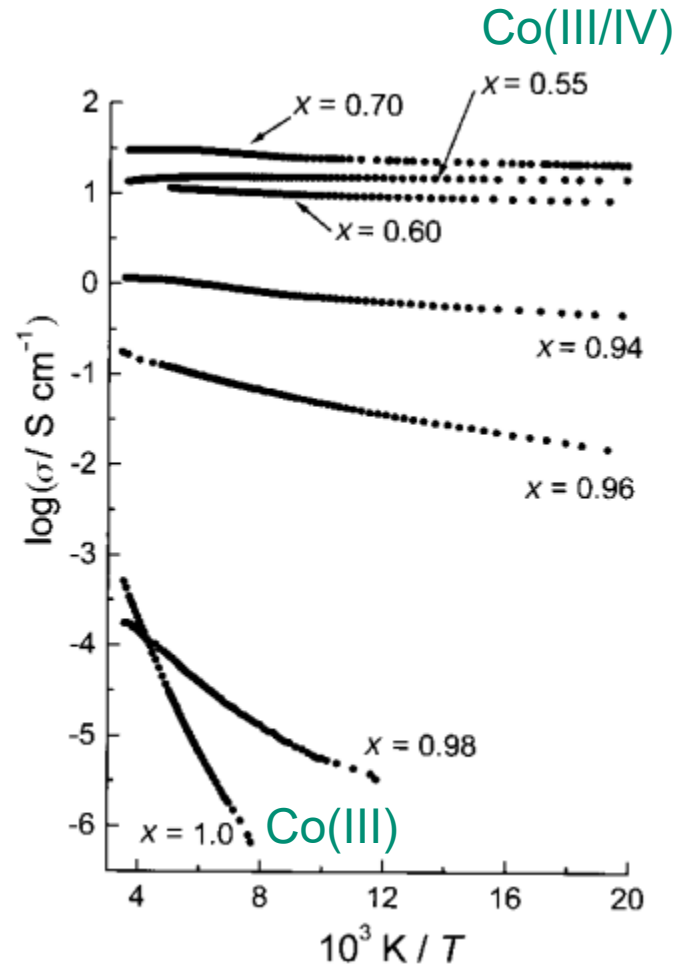
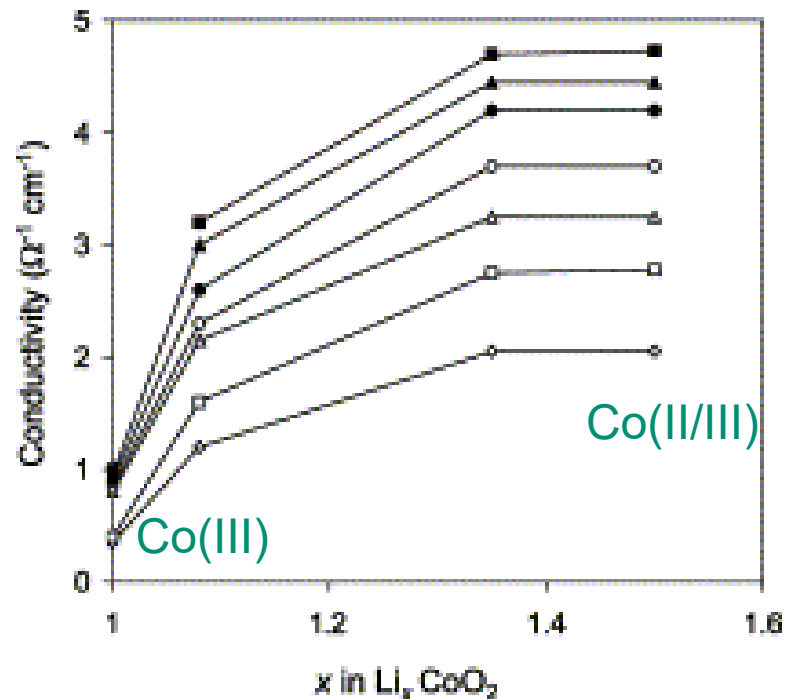
Franchini, C.; Reticioli, M.; Setvin, M.; Diebold, U. *Nat. Rev. Mater.* **2021**, 6, 560-586.

Big Picture Question



What is the relationship between redox state and electronic conductivity in mixed-valence materials?

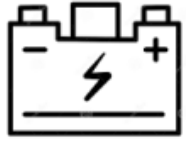
Example: Li_xCoO_2



Electrochemical Random Access Memory (ECRAM)



Battery

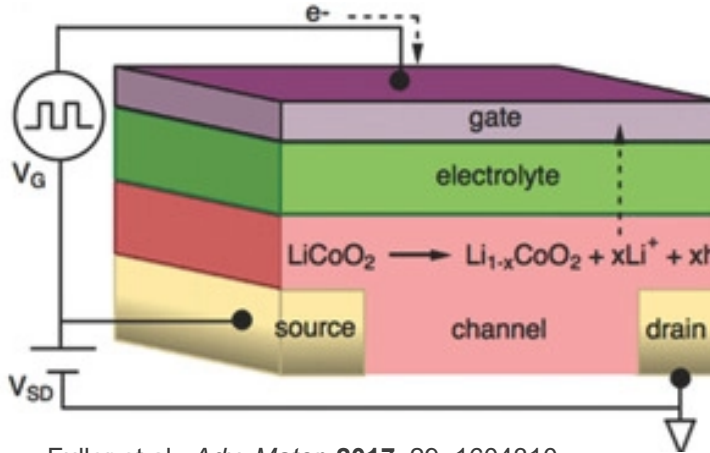


Transistor

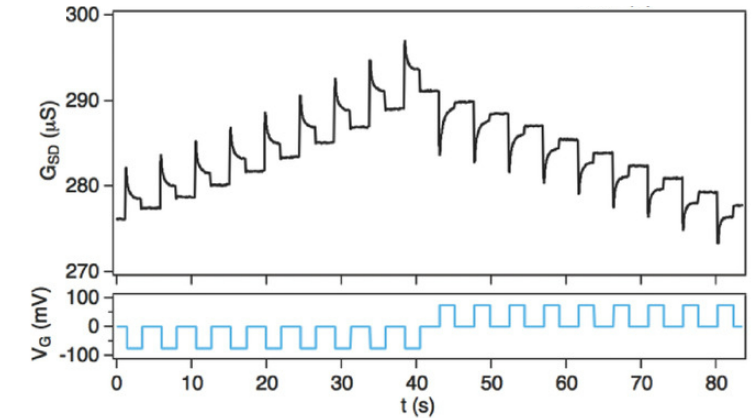


ECRAM

- ECRAM combines principles of bulk charge storage with electrochemical transistor operation.
- Stored charge $\rightarrow$ stored conductance.
- Conductance change represents synaptic weight update.



Fuller et al., *Adv. Mater.* **2017**, 29, 1604310.



	FET	RRAM	ECRAM
Design	3-terminal, dielectric	2-terminal	3-terminal, electrolyte
Switching mechanism	Field effect	Phase-change, conductive filament	Electrochemical doping (electron transfer, ion insertion)
Changes to channel conductivity	Localized near interface	Localized at phase-change regions	Homogeneous
Timeline: first functional devices	1940s	1960s	2017

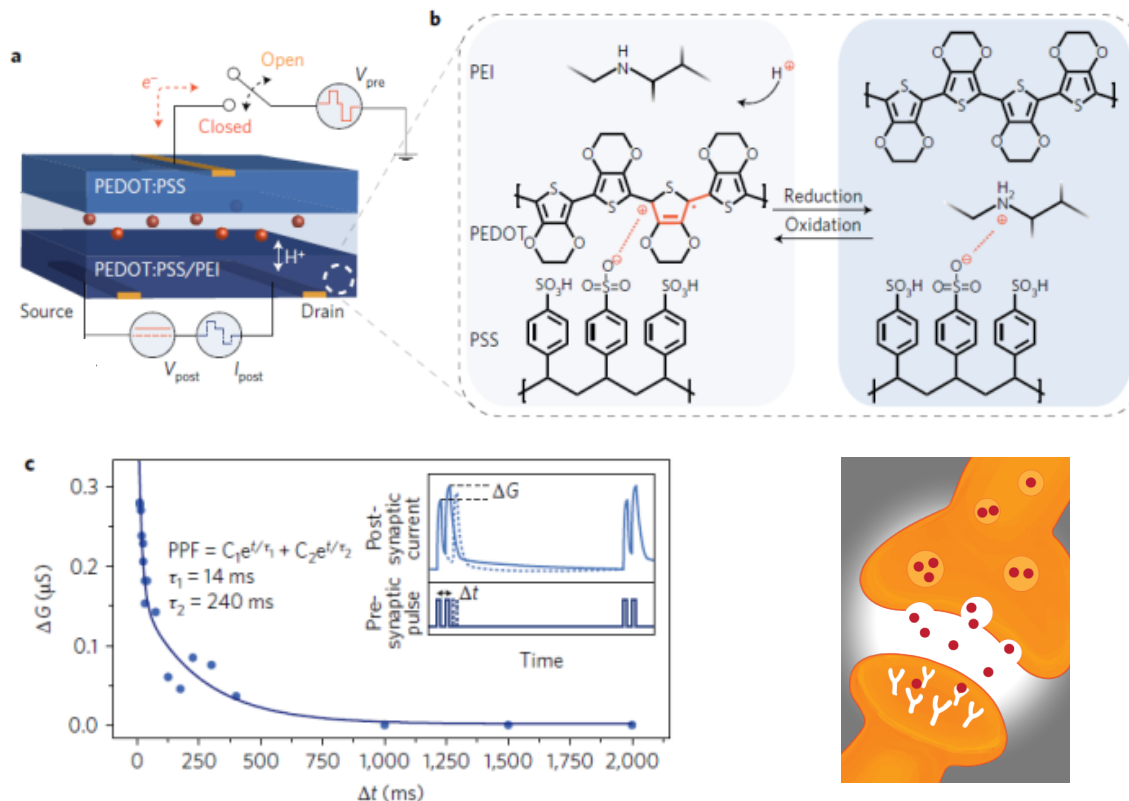
Practical Motivation: Analog Circuits for Neuromorphic Computing



Problem: Conventional hardware for driving neural network computations (CMOS integrated circuits) are inefficient.

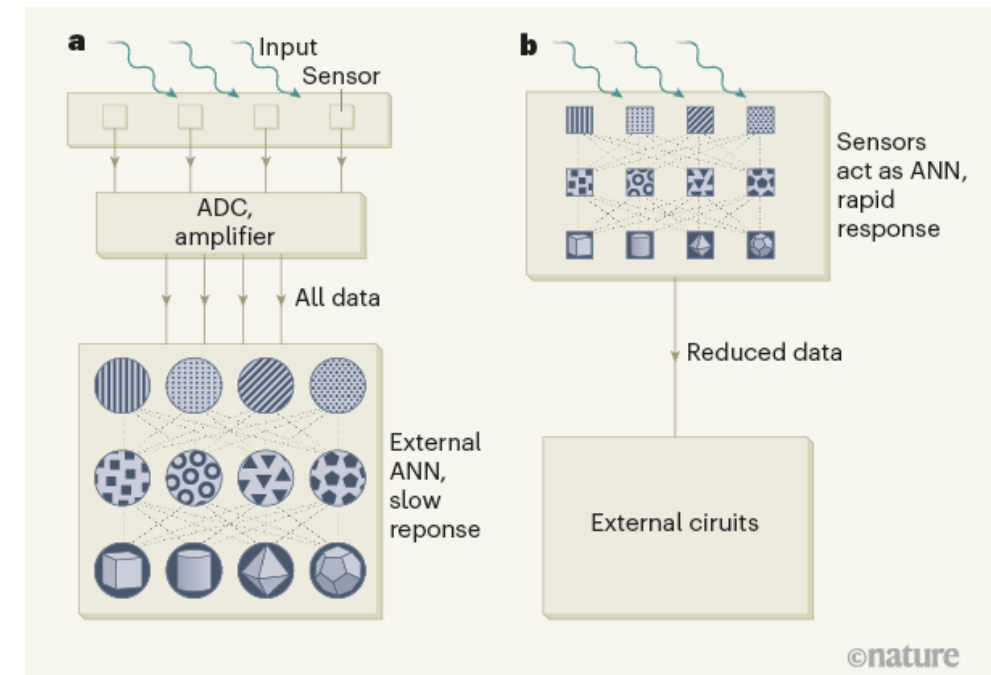
Solution: New concepts for all-analog computation.

- Physical neural networks: Artificial neurons, [artificial synapses](#)



van de Burgt, et al. *Nat. Mater.* **2017**, 16, 414.

Reducing Data Transfer to Improve Vision Sensor Response Time



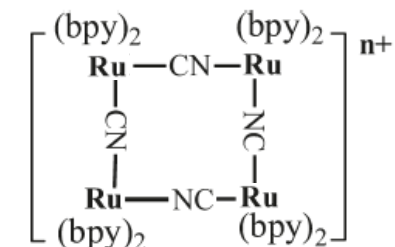
Nature **2020**, 579, 32.

Mennel et al., *Nature* **2020**, 579, 62.

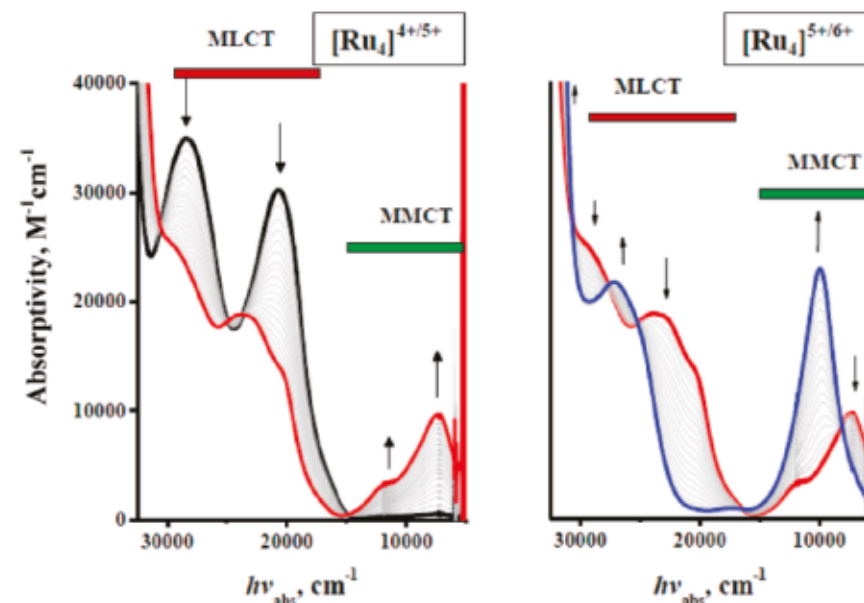
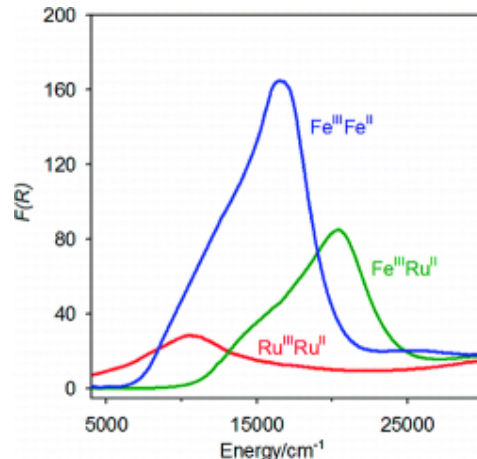
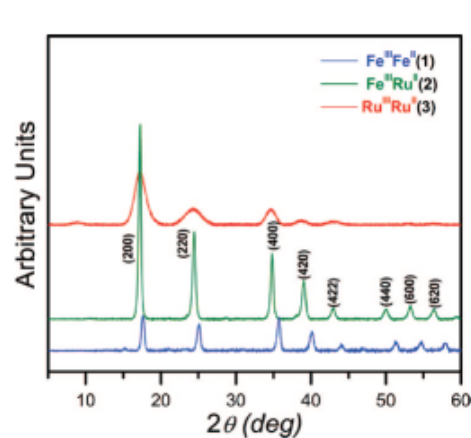
Ruthenium Prussian Blue Analogue (RuPBA)

- Ruthenium Prussian blue analogue (RuPBA) has the highest measured DC conductivity and lowest IVCT energy of the PBA family.

Molecular analogue of RuPBA



Intervalence charge transfer (IVCT)

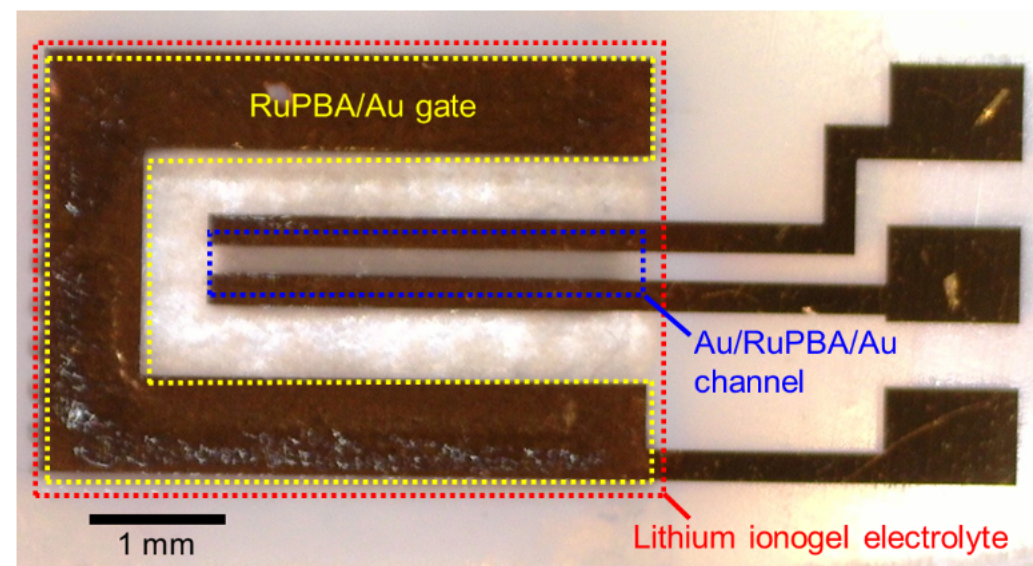
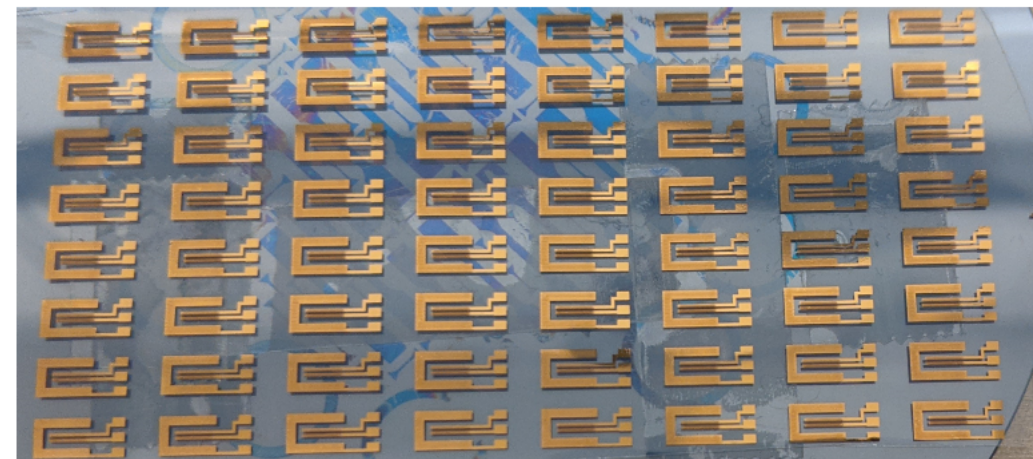
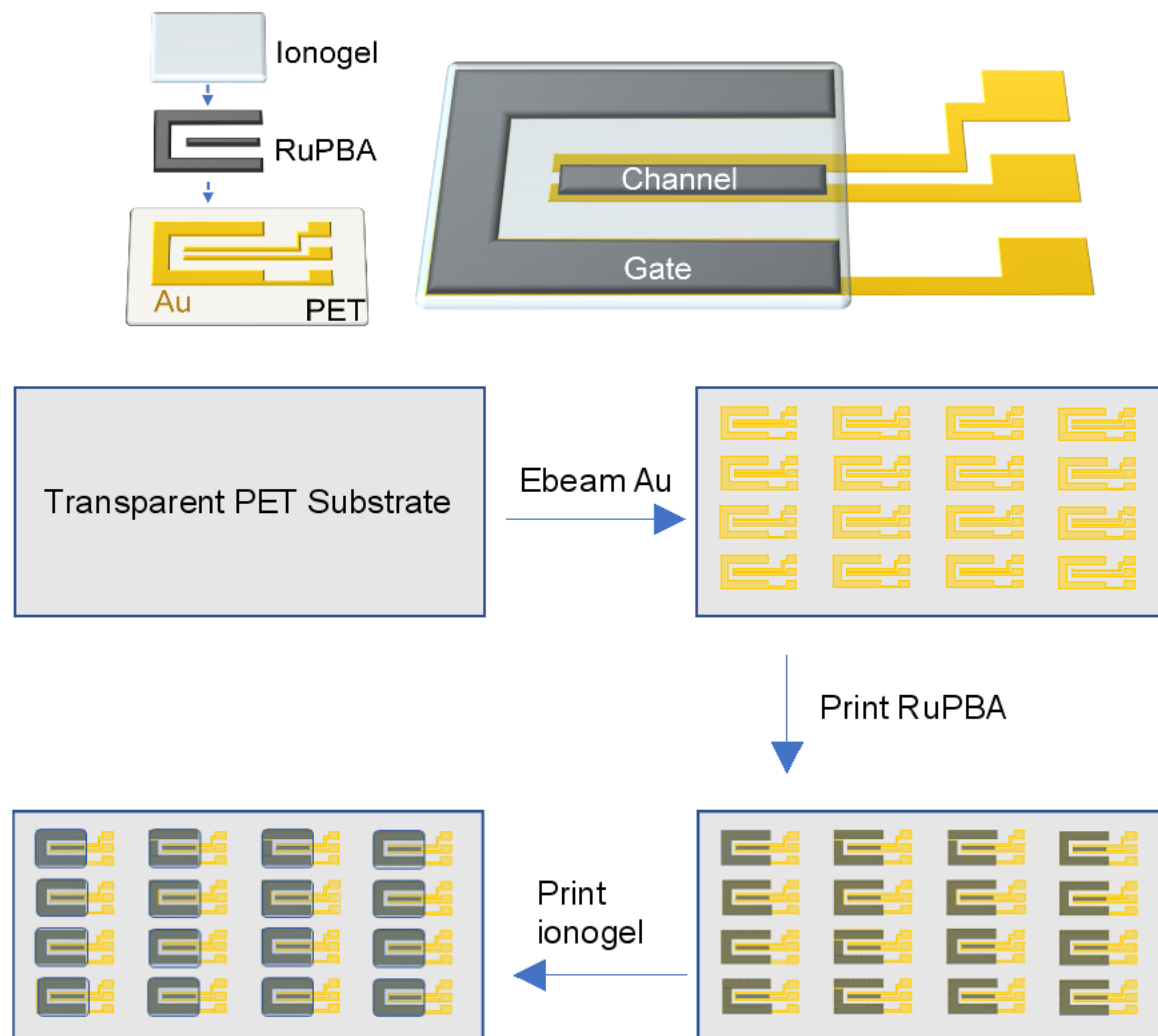


Lin et al., *Inorg. Chem.* **2011**, 50, 8274.

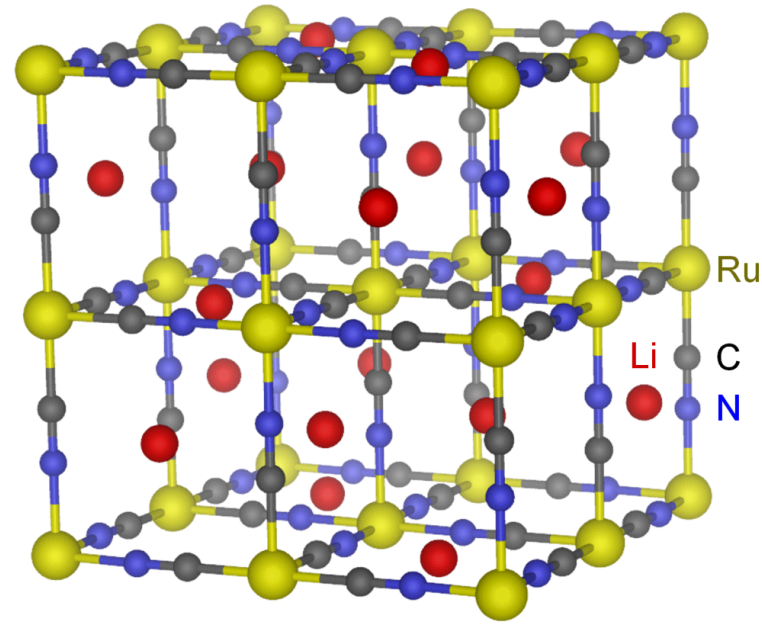
compound	lattice constant (Å)	band manifold (cm ⁻¹)	electrical conductivity ^d (S/cm)
Fe ₄ [Fe(CN) ₆] ₃ ·14H ₂ O (1)	10.16	16 210	5.57 × 10 ⁻⁵
Fe ₄ [Ru(CN) ₆] ₃ ·18H ₂ O (2)	10.42	20 180	5.05 × 10 ⁻⁶
K _{1.2} Ru _{3.6} [Ru(CN) ₆] ₃ ·16H ₂ O (3)	~10.6 ^e	9980	5.69 × 10 ⁻³

- Molecular analogues exhibit Class II/III properties (localized-delocalized transition).

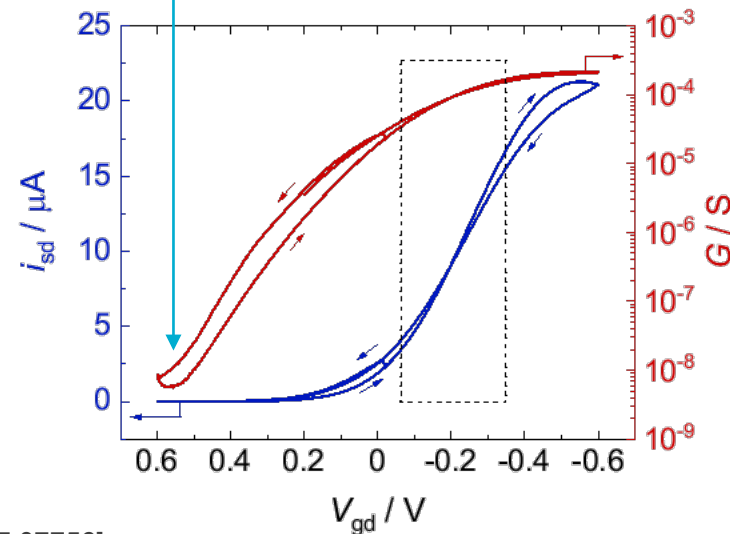
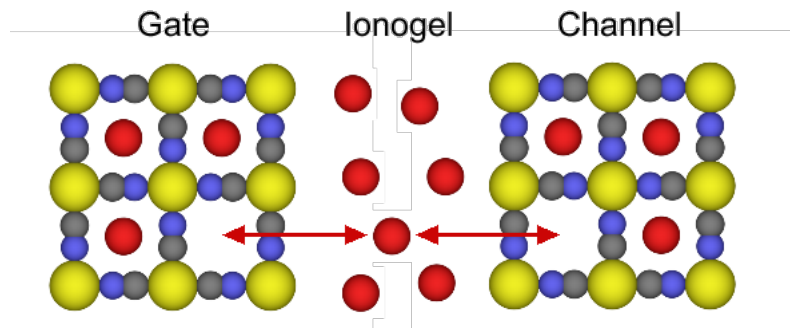
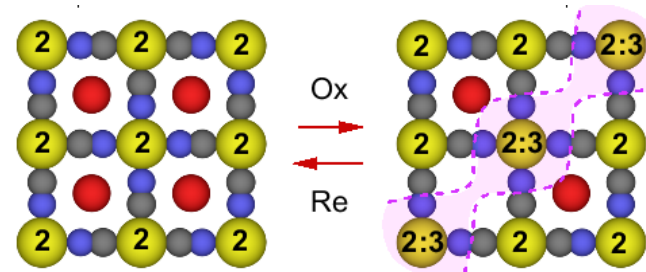
RuPBA ECRAM Device Fab/Architecture



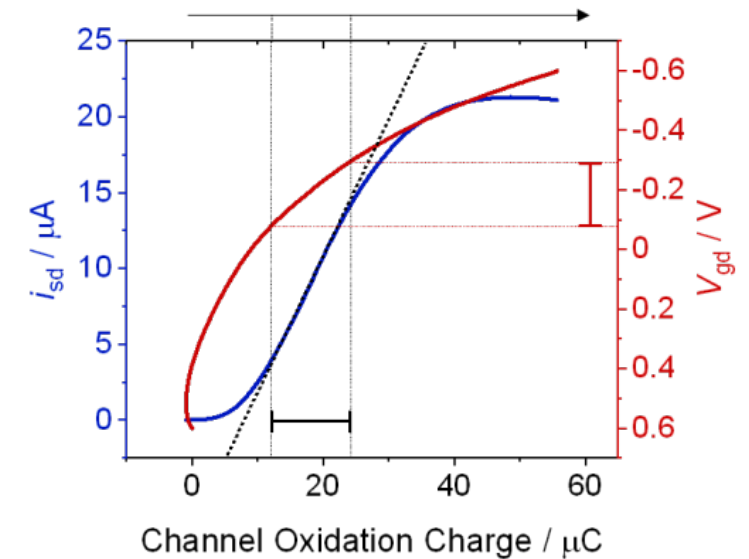
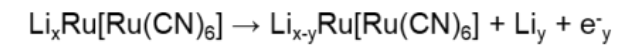
Steady State Transfer Characteristics



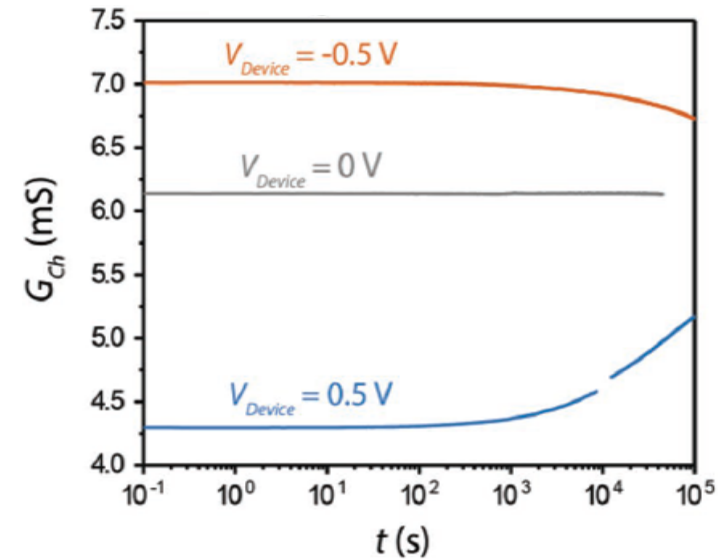
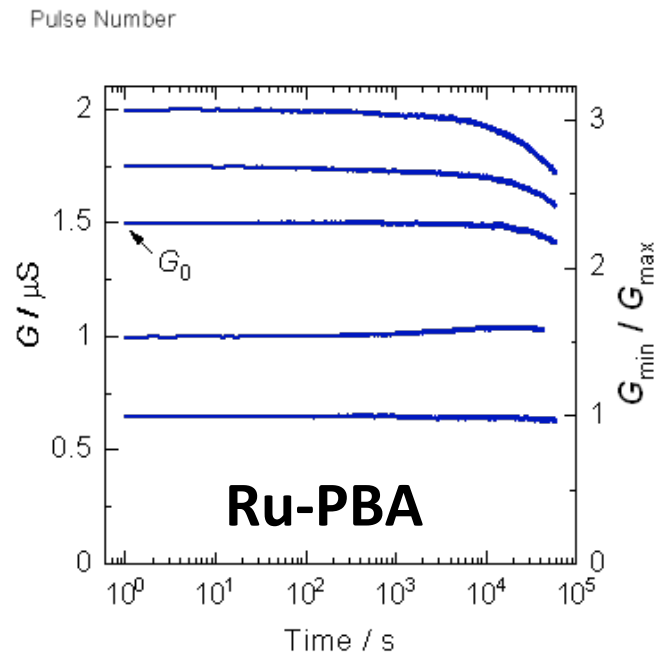
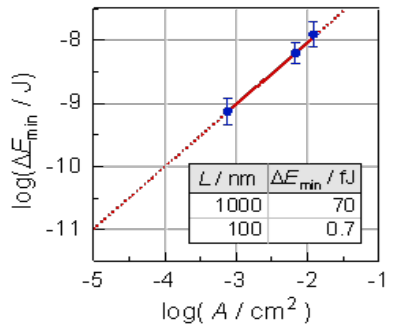
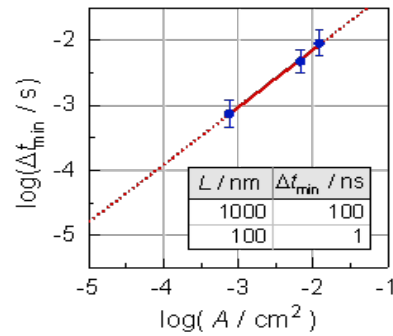
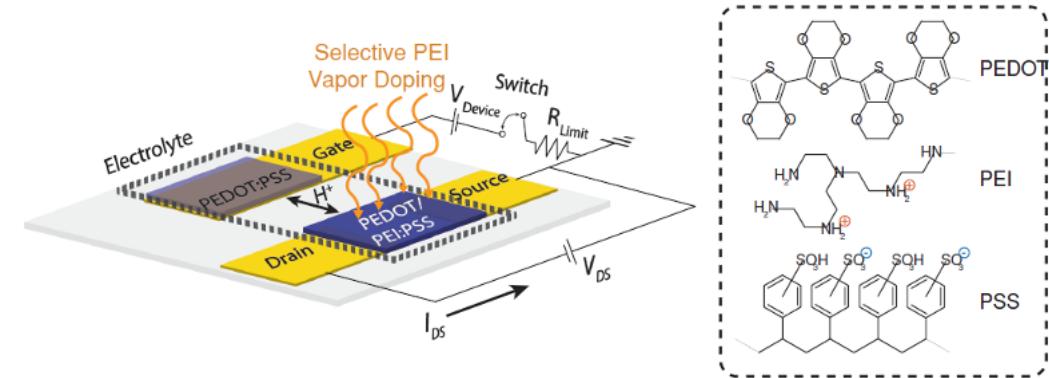
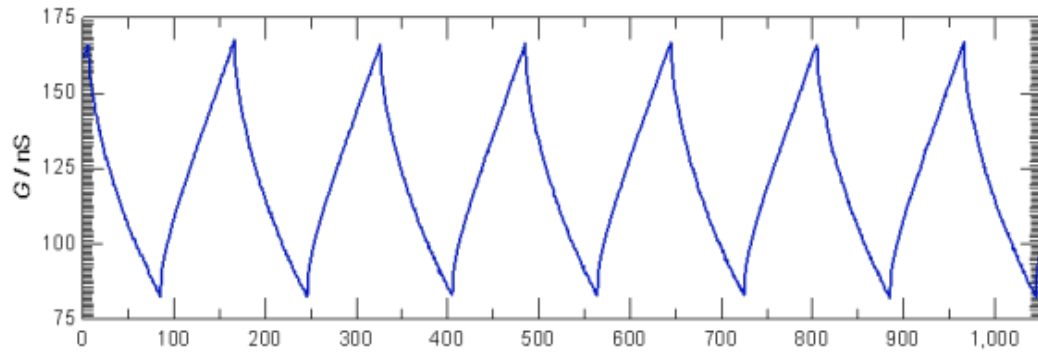
ECRAM Device Channel



- P-type, holes as principle carriers
- 4 orders of magnitude tunability in conductance
- Linear relationship with faradaic charge
 - Stored charge $\rightarrow$ stored conductance
 - Ideal for programming synapses

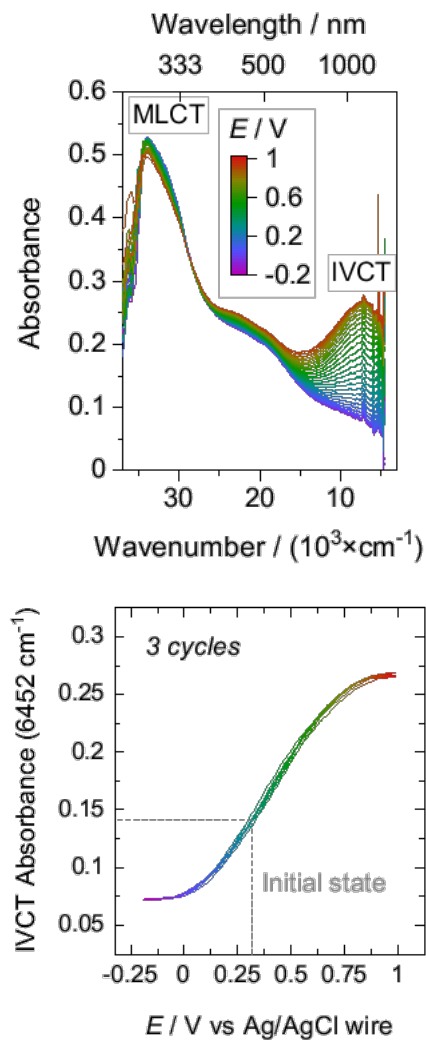


ECRAM Device Performance

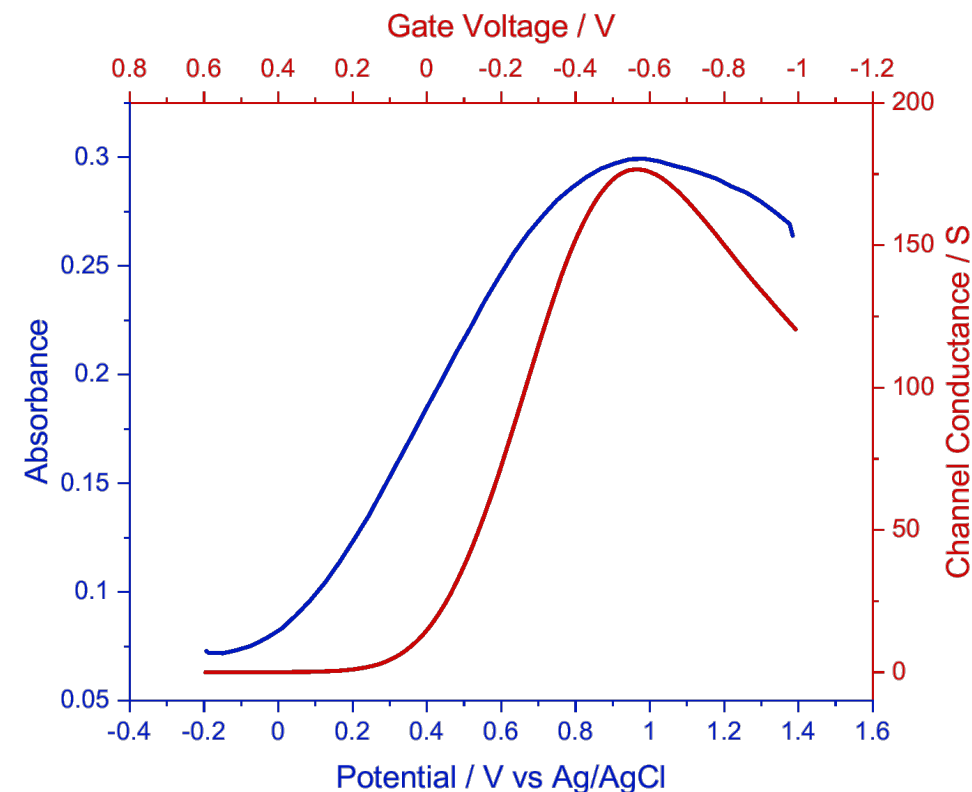
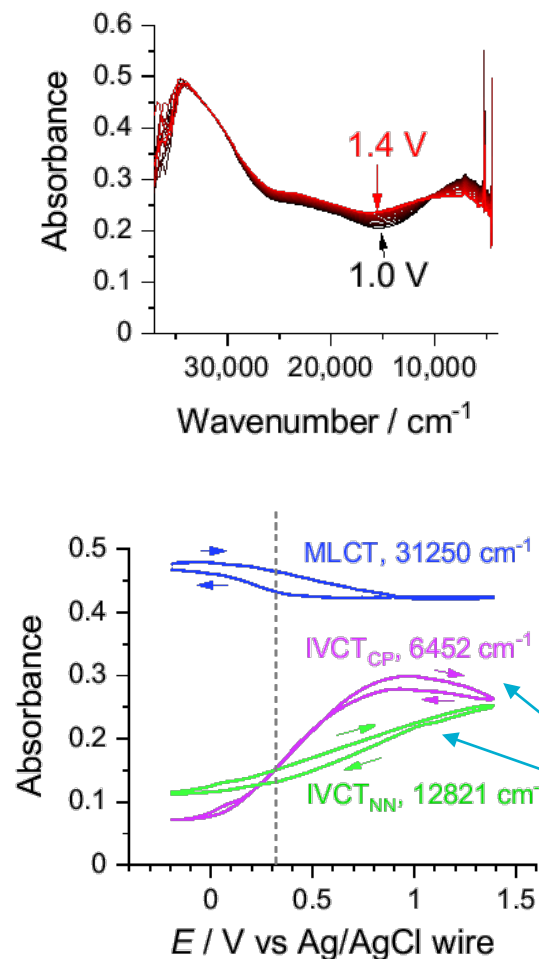




Reversible Range

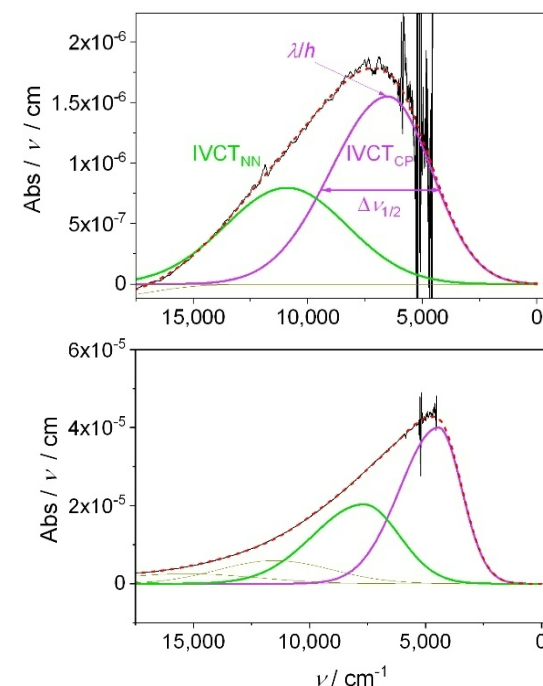
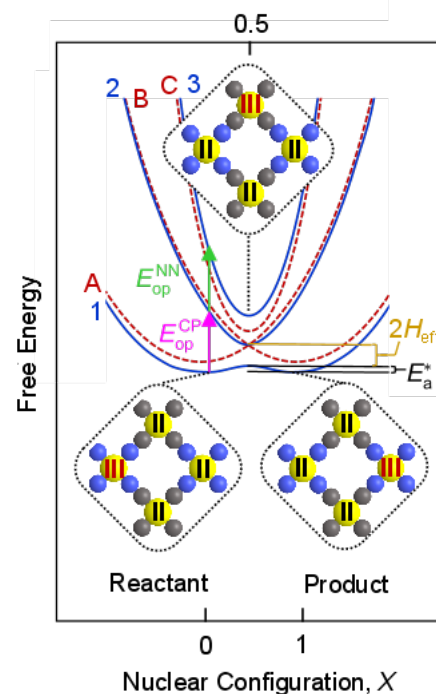
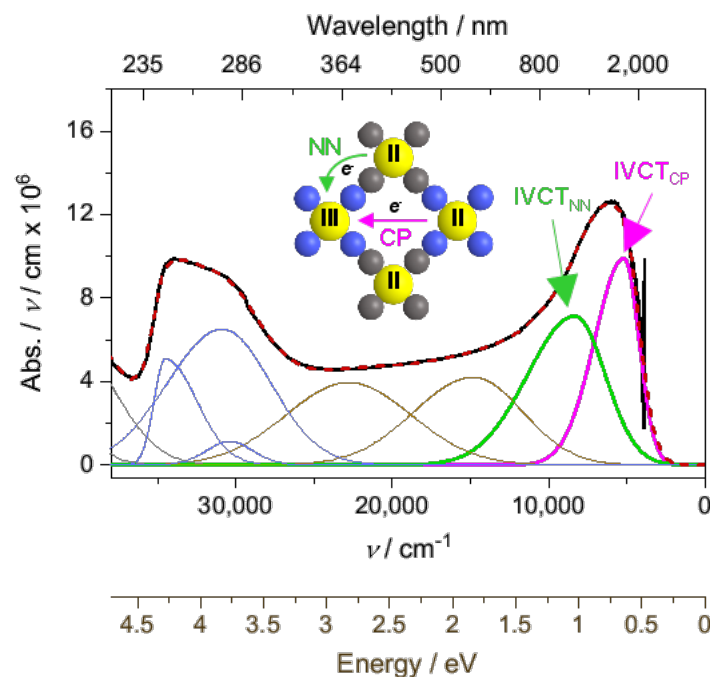


Higher RuPBA Oxidation States



Spectroelectrochemical trends indicate more than one IVCT pathway.

Spectroscopic Insight into Conduction Mechanism



$E = 0 \text{ V}$

$E = 1 \text{ V}$

$$\Delta\nu_{1/2} = [4\ln(2)\lambda k_B T]^{1/2} + \lambda - 2H_{\text{eff}}$$

$$E_a^* = \frac{(\lambda - 2H_{\text{eff}})^2}{4\lambda}$$

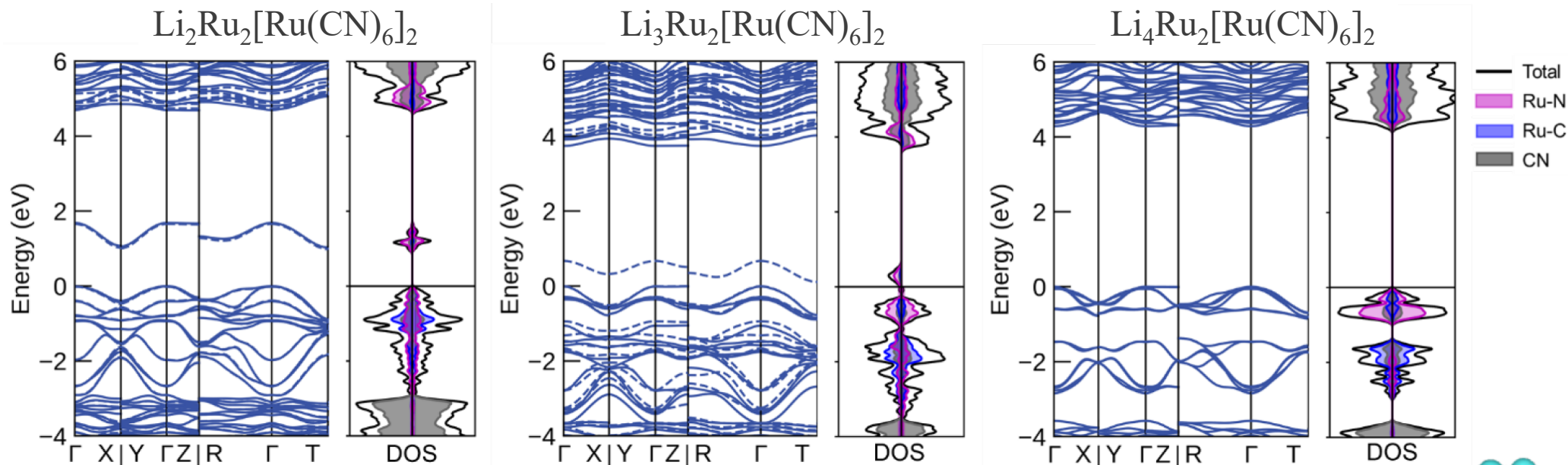
$$k_{\text{ct}} = \kappa \nu_n \exp(-E_a^*/k_B T)$$

$$\mu_h = ed^2 k_{\text{ct}} / 2k_B T$$

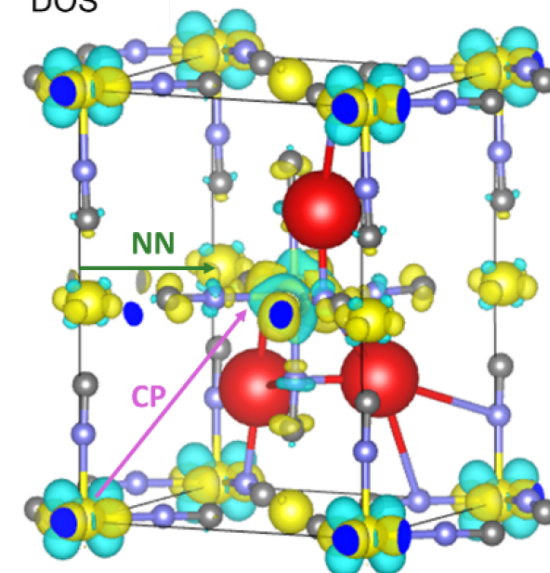
Approximated Parameters Derived from Crosspoire IVCT Analysis

E / V	λ / eV	$h\Delta\nu_{1/2}$ / eV	H_{eff} / eV	E_a^* / meV	$\nu_{\text{el}} / 10^{14}\text{s}^{-1}$	$k_{\text{ct}} / 10^{12}\text{s}^{-1}$	$\mu_h / \text{cm}^2\text{V}^{-1}\text{s}^{-1}$
0.00	0.81	0.64	0.20	50	7.6	8.9	0.95
0.05	0.76	0.50	0.25	24	12	25	2.7
0.10	0.74	0.45	0.26	16	13	34	3.7
0.15	0.66	0.39	0.24	11	12	41	4.3
0.30	0.59	0.36	0.22	11	10	42	4.5
0.60	0.51	0.34	0.18	11	7.5	41	4.3
1.00	0.55	0.39	0.18	17	7.3	33	3.5

Mechanism: DFT Computation

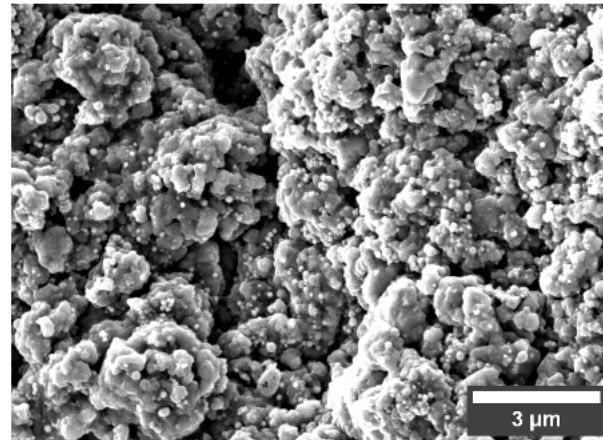
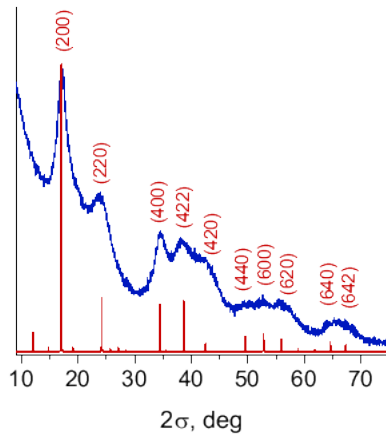
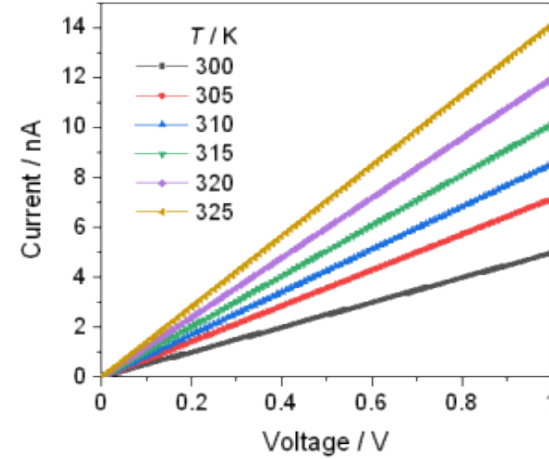
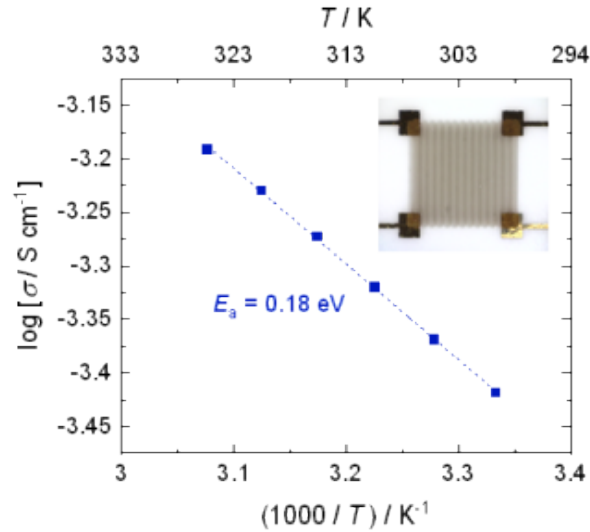


Ru Formal Oxidation State	Lattice Constants (Å)			Band Gap (eV)		Effective Mass
	a	b	c	direct	indirect	
2.5	7.269	7.293	10.334	1.26	0.98	0.70
2.25	7.415	7.217	10.295	0.50	0.10	0.41
2	7.543	7.038	10.180	4.29	4.29	0.52



- $\text{Li}_3\text{Ru}_2[\text{Ru}(\text{CN})_6]_2$ predicted to have a hole mobility of $5 \text{ cm V}^{-1} \text{ s}^{-1}$, compared to $4 \text{ cm V}^{-1} \text{ s}^{-1}$ determined spectroscopically.

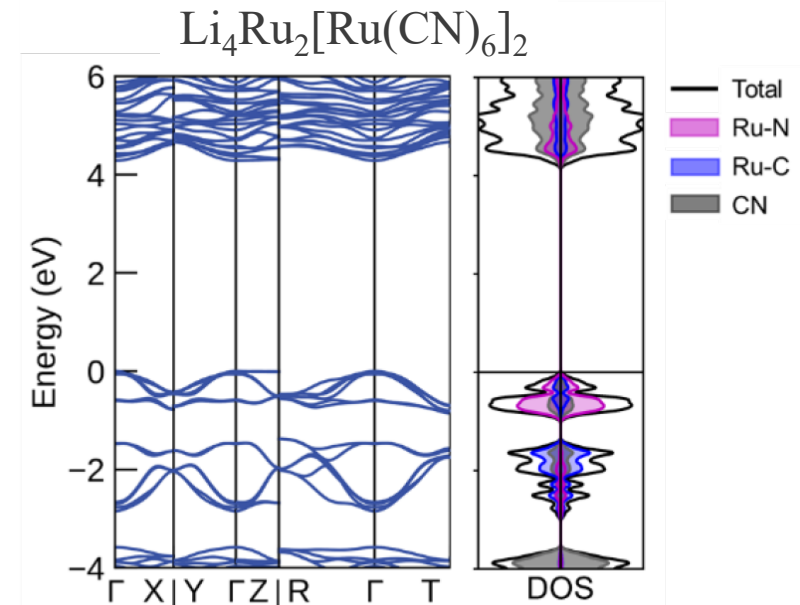
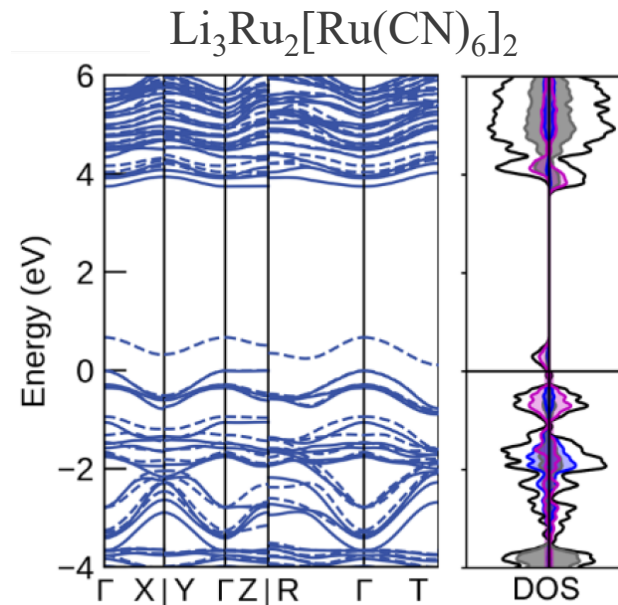
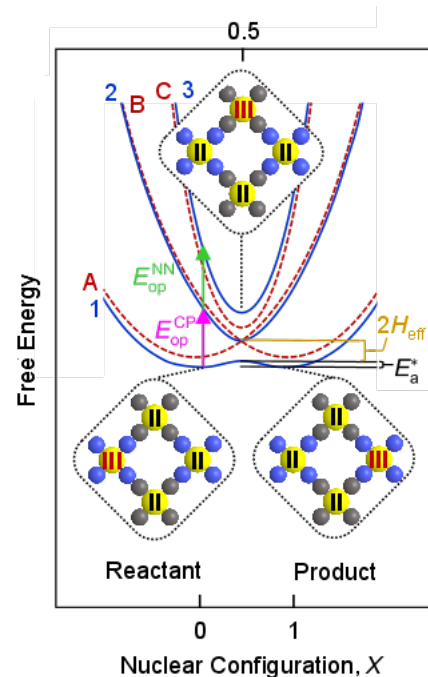
Challenges Going Forward



- Activation energy is relatively low for a PBA, but $\sim 10\times$ higher than predicted.
- Charge transfer at grain boundaries likely requires larger activation energy than in bulk.

Conclusion

- New potential application for extended coordination compounds such as PBAs in neuromorphic computing via ECRAM.
- Working hypothesis for nearest-neighbor and cross-pore IVCT pathways involved in electron hole concentration and mobility, supported by DFT and electron transfer theory.



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Coworkers

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- Deanna D'Alessandro, University of Sydney



Thank you!